EEEB273 - Quiz 3 [Question Set 1] SEMESTER 1, ACADEMIC YEAR 2011/2012 Date: 20 June 2011

Name:	Dr JBO
Student ID Number:	Model Answer
Section: 01A/01B	
Lecturer: Dr. Jamaludin Bin Omar	

Question:

For a MOSFET current source shown in Figure 1, the bias voltages are $V^+ = +2.5$ V and $V^- = 0$ V. Transistors are available with parameters: $k_n = 120 \mu A / V^2$, $V_{TN} = 0.4$ V, and $\lambda = 0$. **Design** the circuit such that $I_{REF} = 120 \mu A$, $I_O = 60 \mu A$, and $V_{DS2}(\text{sat}) = 0.4$ V.

[10 marks]



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Question:

For a MOSFET current source shown in Figure 1, the bias voltages are $V^+ = +2.5$ V and $V^- = 0$ V. Transistors are available with parameters: $k_n = 120 \mu A / V^2$, $V_{TN} = 0.4$ V, and $\lambda = 0$. **Design** the circuit such that $I_{REF} = 100 \mu A$, $I_O = 50 \mu A$, and $V_{DS2}(\text{sat}) = 0.4$ V.

[10 marks]



EEEB273 - Quiz 3 [Question Set 2] SEMESTER 1, ACADEMIC YEAR 2011/2012 Date: 20 June 2011 Name:Dr JBOStudent ID Number:Model AnswerSection:05A / 05BLecturer:Dr. Jamaludin Bin Omar

[10 marks]

Question:

For a MOSFET current source shown in Figure 1, the bias voltages are $V^+ = +2.5$ V and $V^- = 0$ V. Transistors are available with parameters: $\vec{k}_n = 100 \ \mu\text{A} / V^2$, $V_{TN} = 0.4$ V, and $\lambda = 0$. **Design** the circuit such that $I_{REF} = 110 \ \mu\text{A}$, $I_O = 60 \ \mu\text{A}$, and $V_{DS2}(\text{sat}) = 0.4$ V.



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[10 marks]

Question:

For a MOSFET current source shown in Figure 1, the bias voltages are $V^+ = +2.5$ V and $V^- = 0$ V. Transistors are available with parameters: $\vec{k}_n = 110 \ \mu\text{A} / V^2$, $V_{TN} = 0.4$ V, and $\lambda = 0$. **Design** the circuit such that $I_{REF} = 100 \ \mu\text{A}$, $I_O = 60 \ \mu\text{A}$, and $V_{DS2}(\text{sat}) = 0.4$ V.



EEEB273 - Quiz 3 [Question Set 4] SEMESTER 1, ACADEMIC YEAR 2011/2012 Date: 20 June 2011 Name:Dr JBOStudent ID Number:Model AnswerSection:05A / 05BLecturer:Dr. Jamaludin Bin Omar

[10 marks]

Question:

For a MOSFET current source shown in Figure 1, the bias voltages are $V^+ = +2.5$ V and $V^- = 0$ V. Transistors are available with parameters: $\dot{k}_n = 100 \ \mu A / V^2$, $V_{TN} = 0.4$ V, and $\lambda = 0$. **Design** the circuit such that $I_{REF} = 120 \ \mu A$, $I_O = 50 \ \mu A$, and $V_{DS2}(\text{sat}) = 0.4$ V.

